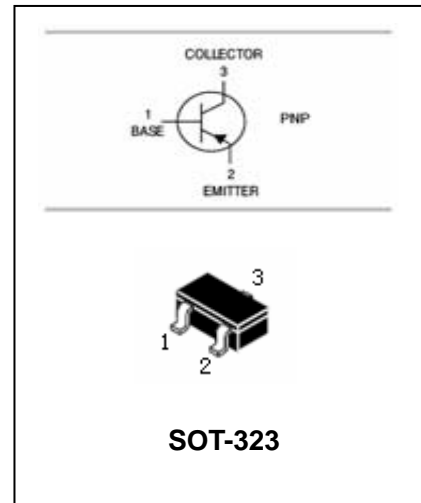


## PNP Silicon Epitaxial Planar Transistor

## 2SA1576A

### FEATURES

- Power dissipation.( $P_C=200\text{mW}$ )
- Excellent  $H_{FE}$  Linearity.
- Complements the 2SC4081.



### APPLICATIONS

- General purpose application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1576A	FQ/FR/FS	SOT-323

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current -Continuous	-150	mA
$P_C$	Collector Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

**PNP Silicon Epitaxial Planar Transistor****2SA1576A****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60V, I_E=0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-6V, I_C=0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-6V, I_C=-1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-5mA$			-0.5	V
Transition frequency	$f_T$	$V_{CE}=-12V, I_C=-2mA$ $f=30MHz$	140			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-12V, I_E=0, f=1MHz$		4	5	pF

**CLASSIFICATION OF  $h_{FE}$** 

Rank	Q	R	S
Range	120-270	180-390	270-560
marking	FQ	FR	FS

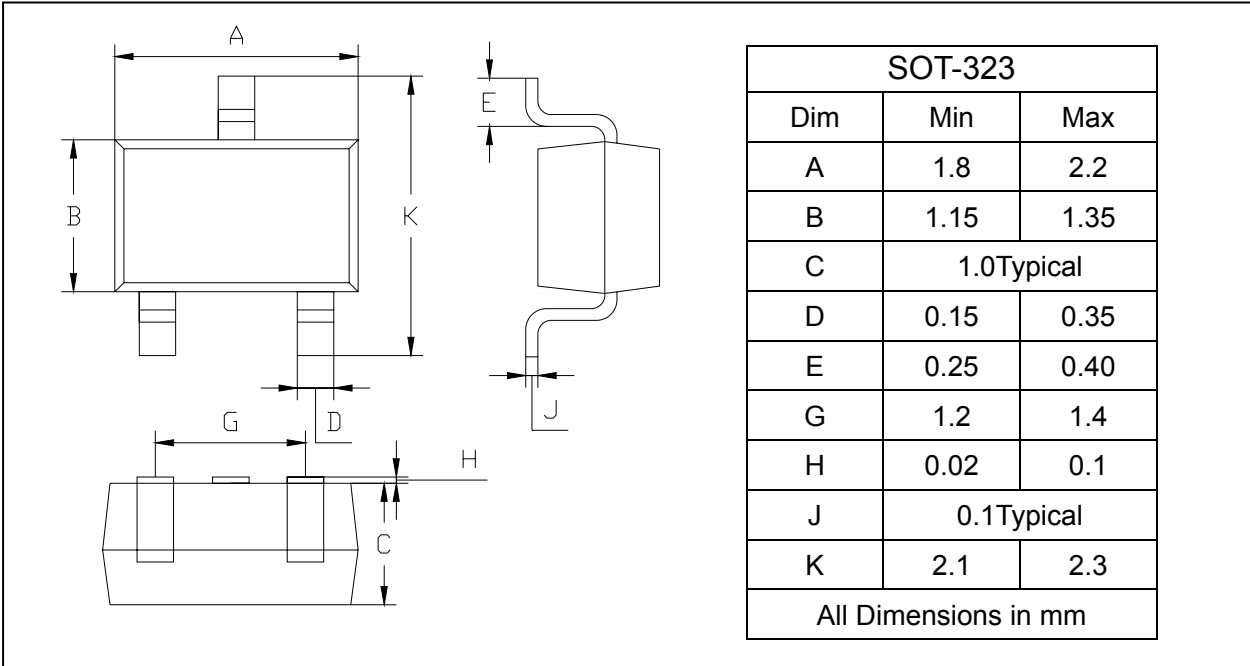
## PNP Silicon Epitaxial Planar Transistor

## 2SA1576A

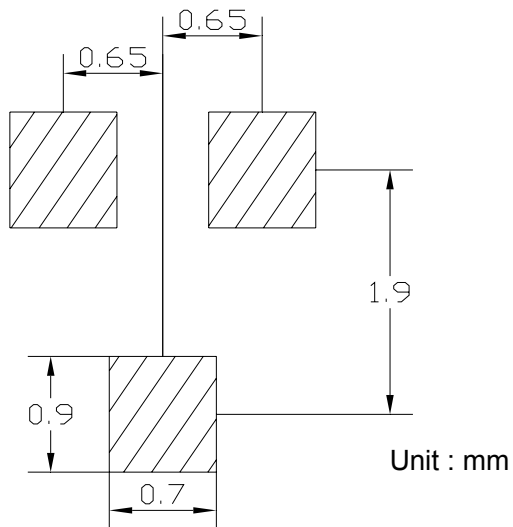
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
2SA1576A	SOT-323	3000/Tape&Reel

[www.s-manuals.com](http://www.s-manuals.com)